

WORKPIECE PROCESSING METHOD

ABSTRACT

Disclosed is a method of processing a workpiece including a mask. The processing method includes: a first process of generating plasma of a first gas containing a silicon halide gas in a processing container of a plasma processing apparatus that accommodates a workpiece having a mask, to form a reactive precursor; a second process of purging a space in the processing container; a third process of generating plasma of a second gas containing oxygen gas in the processing container to form a silicon oxide film; and a fourth process of purging the space in the processing container. In the processing method, a sequence including the first to fourth processes is repeated.

Figure 1